



60V Dual N-Channel Enhancement Mode MOSFET

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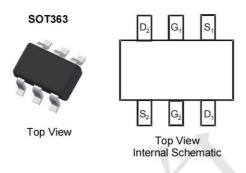
Features

- Fast switching
- Green Device Available
- Suit for 1.5V Gate Drive Applications

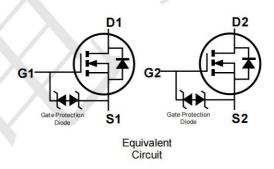
Application

- Notebook
- Load Switch
- Networking
- Hand-held Instruments

Package and Pin Configuration



Circuit diagram



Marking: TF △

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current (T450°C)	T _A =25℃	- I _D	0.3	А	
Continuous Drain Current (T _J =150°C)	T _A =100°C		0.19		
Drain Current-Pulsed (Note 1)		I _{DM}	0.8	Α	
Maximum Power Dissipation		P _D	0.35	W	
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	-55 To 150	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	°C/W





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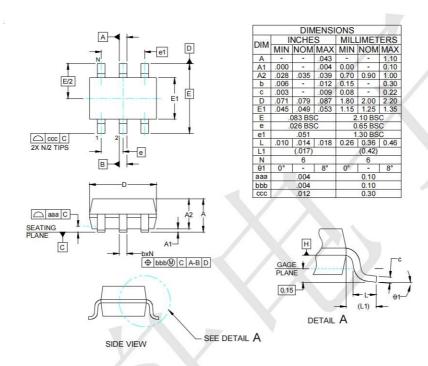
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		1-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Coto Body Looks as Comment	L	V _{GS} =±10V,V _{DS} =0V	-	-	±1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-		±10	uA
On Characteristics (Note 3)	,					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.6	2.5	V
Drain-Source On-State Resistance	D	V _{GS} =4.5V, I _D =0.2A) -	1.9	2.5	Ω
	R _{DS(ON)}	V _{GS} =10V, I _D =0.3A	-	1.8	2.2	Ω
Forward Transconductance	g fs	V _{DS} =10V,I _D =0.2A	0.1	=	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =30V,V _{GS} =0V, F=1.0MHz		27		PF
Output Capacitance	Coss			18		PF
Reverse Transfer Capacitance	C _{rss}	F-1.0WITZ		2		PF
Switching Characteristics (Note 4)			•	•	•	
Turn-on Delay Time	t _{d(on)}		_	10	=	nS
Turn-on Rise Time	tr	V_{DD} =30 V , I_{D} =0.2 A	_	50	1,14	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =10 Ω	-	17	18	nS
Turn-Off Fall Time	t _f		-	10	11-	nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =0.3A, V _{GS} =4.5V	-	1.7	3	nC
Drain-Source Diode Characteristics			*			7.0
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	0.3	Α

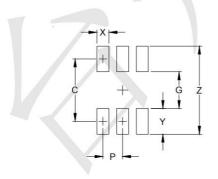


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Outline Drawing - SOT-363(2.0X2.1)



Land Pattern - SOT-363



DIMENSIONS			
DIM	INCHES	MILLIMETERS	
С	(.073)	(1.85)	
G	.039	1.00	
Р	.026	0.65	
X	.016	0.40	
Y	.033	0.85	
7	106	2.70	

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